UNISONIC TECHNOLOGIES CO., LTD

UBCX56

NPN EPITAXIAL SILICON TRANSISTOR

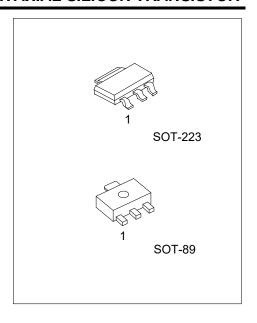
NPN MEDIUM POWER TRANSISTORS

DESCRIPTION

The UTC UBCX56 is an NPN epitaxial silicon transistor, it uses UTC's advanced technology to provide customers high DC current gain and high current capacity.

FEATURES

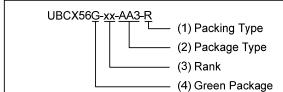
- * High Current Capacity
- * High DC Current Gain



ORDERING INFORMATION

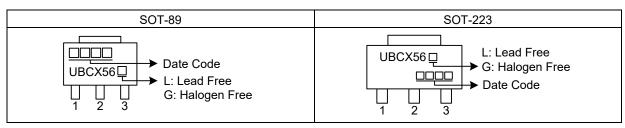
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UBCX56L-xx-AA3-R	UBCX56G-xx-AA3-R	SOT-223	В	С	Е	Tape Reel	
UBCX56L-xx-AB3-R	UBCX56G-xx-AB3-R	SOT-89	В	С	Е	Tape Reel	

Pin Assignment: B: Base C: Collector E: Emitter Note:



- (1) R: Tape Reel
- (2) AA3: SOT-223, AB3: SOT-89
- (3) xx: refer to Classification of hFE
- (4) G: Halogen Free and Lead Free, L: Lead Free

MARKING



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage (open emitter)		V_{CBO}	100	V
Collector-Emitter Voltage (open base)		V_{CEO}	80	V
Emitter-Base Voltage (open co	ollector)	V_{EBO}	5	V
Collector Current (DC)		Ic	1	Α
Peak Collector Current		I _{CM}	1.5	Α
Peak Base Current		I _{BM}	0.2	Α
Total Power Dissipation	SOT-223	Б	1.5	W
(T _A ≤ 25°C, Note2)	SOT-89	P _D	1.3	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-65 ~ +150	°C
Operating Ambient Temperatu	re	T _{OPR}	-65 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm².

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
	SOT-223	0	83.3	°C/W
Junction to Ambient	SOT-89	ӨЈА	94	°C/W

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_A =25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV _{CBO}	I _C = 100μA, I _E =0	100			V
Collector Emitter Breakdown Voltage	BV_CEO	I _C = 10mA, I _B =0	80			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E =10μA, I _C =0	5			V
Collector Cut-Off Current	I _{CBO}	I _E =0, V _{CB} =30V			100	nA
Emitter Cut-Off Current	I _{EBO}	I _C =0, V _{EB} =5V			100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I _C =500mA, I _B =50mA			0.5	V
Base-Emitter Voltage	V_{BE}	I _C =500mA, V _{CE} =2V			1	V
	h _{FE1}	V _{CE} =2V, I _C =5mA	40			
DC Current Gain	h _{FE2}	V _{CE} =2V, I _C =150mA	63		250	
	h _{FE3}	V _{CE} =2V, I _C =500mA	25			

■ CLASSIFICATION OF h_{FE2}

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RANK	10	16
RANGE	63 ~ 100	100 ~ 250

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